



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Features

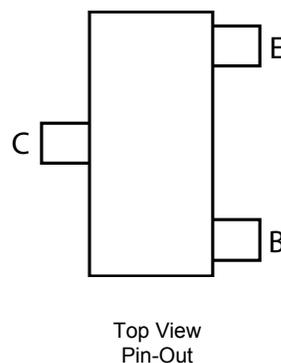
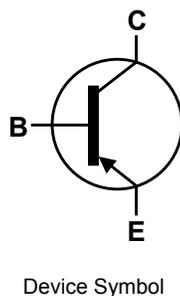
- $BV_{CEO} > -70V$
- $I_C = -1.5A$ Continuous Collector Current
- $I_{CM} = -3A$ Peak Pulse Current
- Low Saturation Voltage $V_{CE(sat)} < -220mV @ -1A$
- $R_{CE(SAT)} = 140m\Omega$ for a low equivalent on-resistance
- 625mW power dissipation
- h_{FE} characterised up to -3A for high current gain hold-up

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208 
- Weight 0.008 grams (approximate)

Applications

- High-side driver
- Load disconnect switch
- Motor drive



Maximum Ratings (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CBO}	-70	V
Collector-Emitter Voltage	V_{CEO}	-70	V
Emitter-Base Voltage	V_{EBO}	-7	V
Continuous Collector Current	I_C	-1.5	A
Peak Pulse Current	I_{CM}	-3	A
Base Current	I_B	-500	mA

Thermal Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

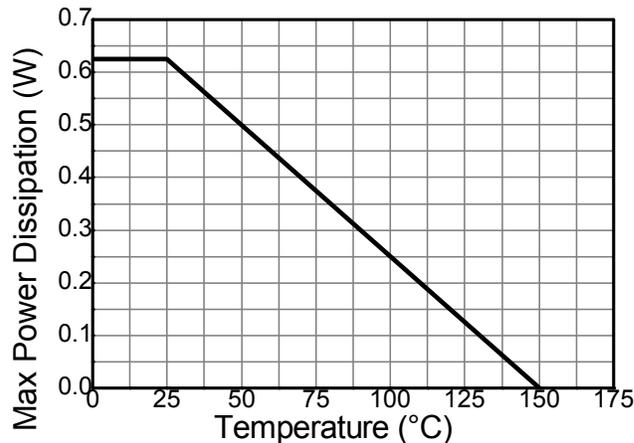
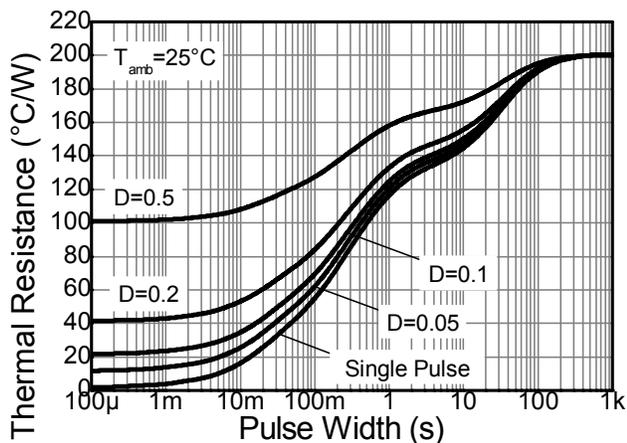
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 6)	P_D	625	mW
Power Dissipation (Note 7)	P_D	806	mW
Thermal Resistance, Junction to Ambient (Note 6)	$R_{\theta JA}$	200	$^\circ\text{C/W}$
Thermal Resistance, Junction to Ambient (Note 7)	$R_{\theta JA}$	155	$^\circ\text{C/W}$
Thermal Resistance, Junction to Leads (Note 8)	$R_{\theta JL}$	194	$^\circ\text{C/W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^\circ\text{C}$

ESD Ratings (Note 9)

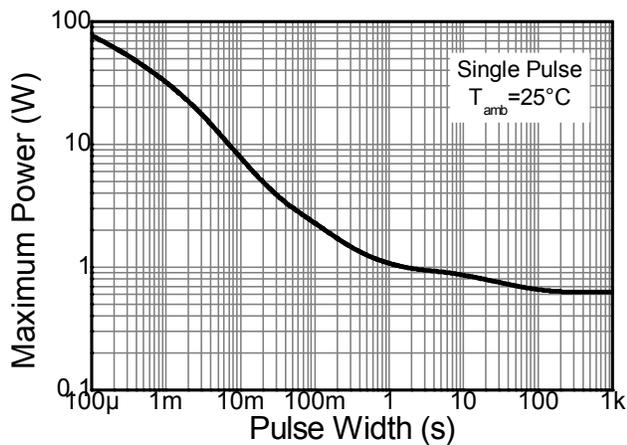
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

- Notes:
6. For a device surface mounted on 25mm X 25mm FR4 PCB with high coverage of single sided 1 oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 7. Same as note 6, except the device is measured at $t \leq 5$ sec.
 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

Thermal Characteristics and Derating information

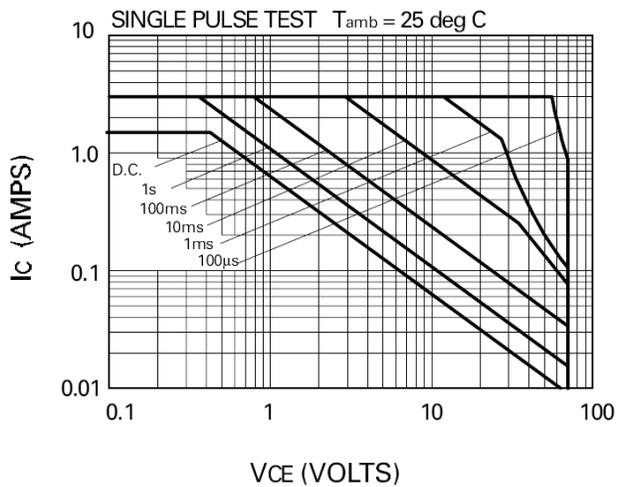


Transient Thermal Impedance



Pulse Power Dissipation

Derating Curve



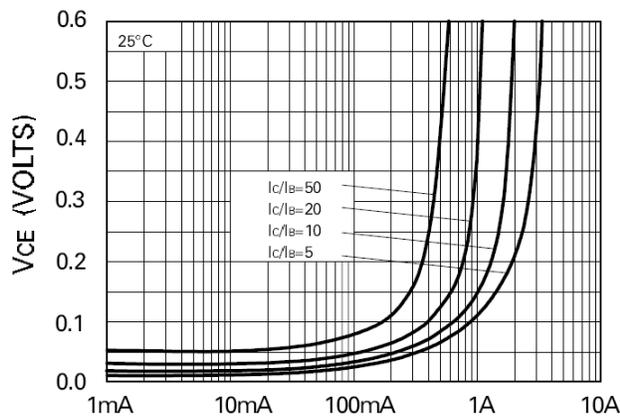
Safe Operating Area

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

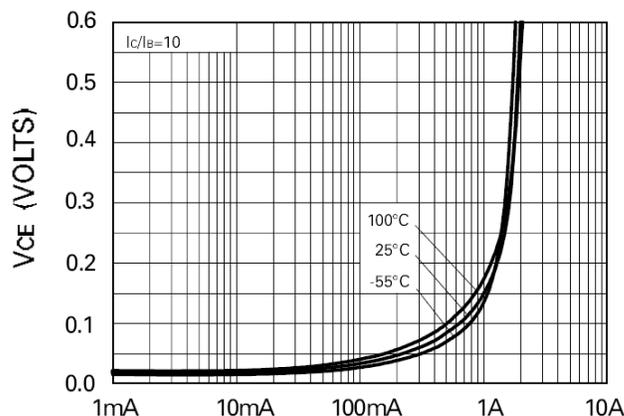
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	-70	-150	-	V	$I_C = -100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 10)	BV_{CEO}	-70	-125	-	V	$I_C = -10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	-7	-8.8	-	V	$I_E = -100\mu\text{A}$
Collector Cutoff Current	I_{CBO}	-	<1	-100	nA	$V_{CB} = -60\text{V}$
Emitter Cutoff Current	I_{EBO}	-	<1	-100	nA	$V_{EB} = -5.6\text{V}$
Collector Emitter Cutoff Current	I_{CES}	-	<1	-100	nA	$V_{CE} = -60\text{V}$
Static Forward Current Transfer Ratio (Note 10)	h_{FE}	300	470	-	-	$I_C = -10\text{mA}, V_{CE} = -5\text{V}$
		300	450	-		$I_C = -0.1\text{A}, V_{CE} = -5\text{V}$
		175	275	-		$I_C = -1\text{A}, V_{CE} = -5\text{V}$
		40	60	-		$I_C = -1.5\text{A}, V_{CE} = -5\text{V}$
		-	10	-		$I_C = -3\text{A}, V_{CE} = -5\text{V}$
Collector-Emitter Saturation Voltage (Note 10)	$V_{CE(sat)}$	-	-35	-50	mV	$I_C = -0.1\text{A}, I_B = -10\text{mA}$
		-	-135	-200		$I_C = -0.5\text{A}, I_B = -20\text{mA}$
		-	-140	-220		$I_C = -1\text{A}, I_B = -100\text{mA}$
		-	-175	-260		$I_C = -1.5\text{A}, I_B = -200\text{mA}$
Base-Emitter Turn-On Voltage(Note 10)	$V_{BE(on)}$	-	-0.78	-1.0	V	$I_C = -1.5\text{A}, V_{CE} = -5\text{V}$
Base-Emitter Saturation Voltage(Note 10)	$V_{BE(sat)}$	-	-0.94	-1.05	V	$I_C = -1.5\text{A}, I_B = -200\text{mA}$
Output Capacitance	C_{obo}	-	14	20	pF	$V_{CB} = -10\text{V}, f = 1\text{MHz}$
Transition Frequency	f_T	150	200	-	MHz	$V_{CE} = -10\text{V}, I_C = -50\text{mA}, f = 100\text{MHz}$
Turn-On Time	t_{on}	-	40	-	ns	$V_{CC} = -50\text{V}, I_C = -0.5\text{A}$
Turn-Off Time	t_{off}	-	700	-	ns	$I_{B1} = I_{B2} = -50\text{mA}$

 Notes: 10. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$

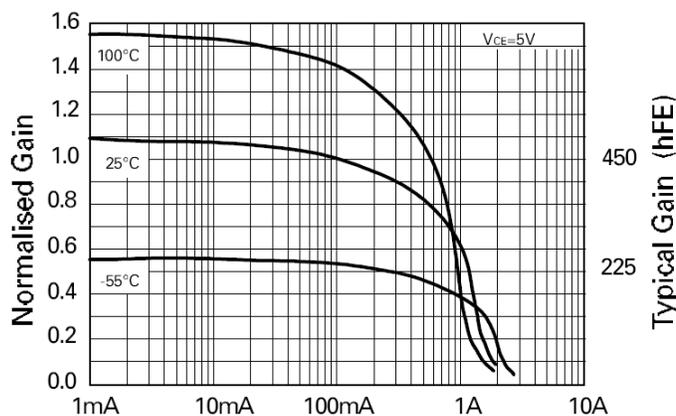
Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)



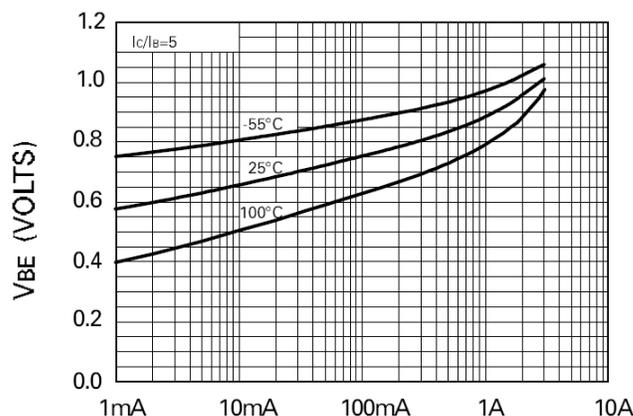
Collector Current
 $V_{BE(SAT)}$ vs I_C



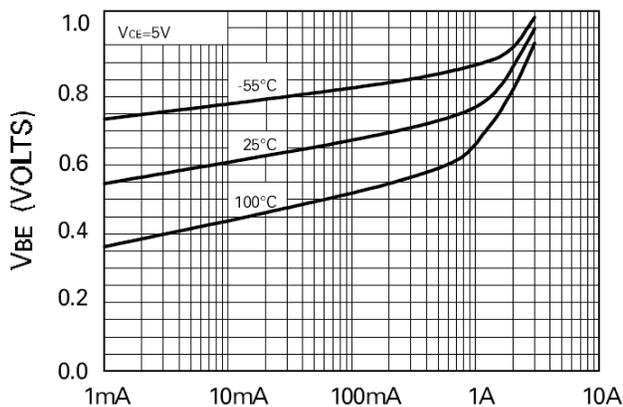
Collector Current
 $V_{CE(SAT)}$ vs I_C



Collector Current
hFE vs I_C

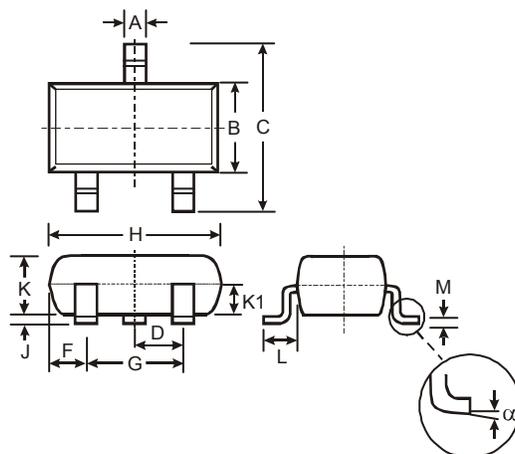


Collector Current
 $V_{BE(SAT)}$ vs I_C



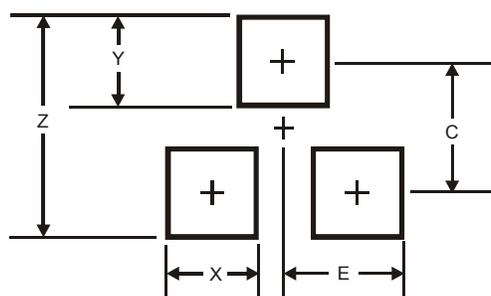
Collector Current
 $V_{BE(ON)}$ vs I_C

Package Outline Dimensions



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35